

**SANYO**

No.819D

**DRA5**

Silicon Diffused Junction Type

5.0A Reverse Blocking Thyristor

**Features**

- Glass passivation for high reliability
- Peak OFF-state (reverse) voltage : -100 to -600V
- Average ON-state current : 5A
- TO-220 package
- Weight : 2g

**Absolute Maximum Ratings at Ta = 25°C**

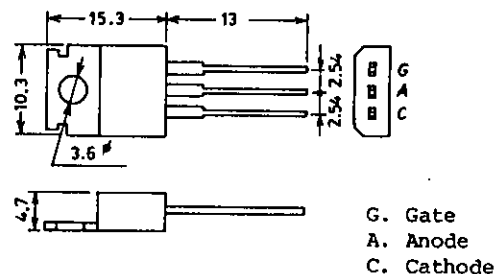
		DRA5B	DRA5C	DRA5E	DRA5G	unit
Repetitive Peak OFF-State Voltage	$V_{DRM}$	100	200	400	600	V
Non-Repetitive Peak Reverse Voltage	$V_{RSM}$	-150	-300	-500	-700	V
Repetitive Peak Reverse Voltage	$V_{RRM}$	-100	-200	-400	-600	V
Average ON-State Current	$I_{T(AV)}$	Tc = 91°C, single-phase half-wave		→	→	5 A
RMS ON-State Current	$I_{T(RMS)}$	→	→	→	→	7.8 A
Surge ON-State Current	$I_{TSM}$	Sine half-wave 1 cycle, 50Hz		→	→	80 A
Amperes Squared-Seconds	$\int i^2 T \cdot dt$	→	→	→	→	32 A <sup>2</sup> S
Peak Gate Power Dissipation	$P_{GM}$	→	→	→	→	5 W
Average Gate Power Dissipation	$P_{G(AV)}$	→	→	→	→	0.5 W
Peak Gate Forward Current	$I_{FGM}$	→	→	→	→	2 A
Peak Gate Forward Voltage	$V_{FGM}$	→	→	→	→	10 V
Peak Gate Reverse Voltage	$V_{RGM}$	→	→	→	→	5 V
Junction Temperature	$T_j$	→	→	→	→	125 °C
Storage Temperature	$T_{stg}$	→	→	→	→	-40 to +125 °C

**Electrical Characteristics at Ta = 25°C**

				min	typ	max	unit
Repetitive Peak OFF-State Current	$I_{DRM}$	Tj = 125°C, $V_D = V_{DRM}$				2	mA
Repetitive Peak Reverse Current	$I_{RRM}$	Tj = 125°C, $V_R = V_{RRM}$				2	mA
ON-State Voltage	$V_T$	$I_T = 15A$				1.6	V
Critical Rate of Rise of OFF-State Voltage	dv/dt	Tc = 125°C, $V_D = 2/3V_{DRM}$	30				V/μs
Holding Current	$I_H$	$R_L = 100\Omega$				60	mA
Gate Trigger Current	$I_{GT}$	$V_D = 6V, R_L = 10\Omega$				40	mA
Gate Trigger Voltage	$V_{GT}$	$V_D = 6V, R_L = 10\Omega$				1.5	V
Gate Nontrigger Voltage	$V_{GD}$	Tc = 125°C, $V_D = 2/3V_{DRM}$	0.2				V
Thermal Resistance	$R_{th(j-c)}$					3	°C/W

**Package Dimensions 1104**

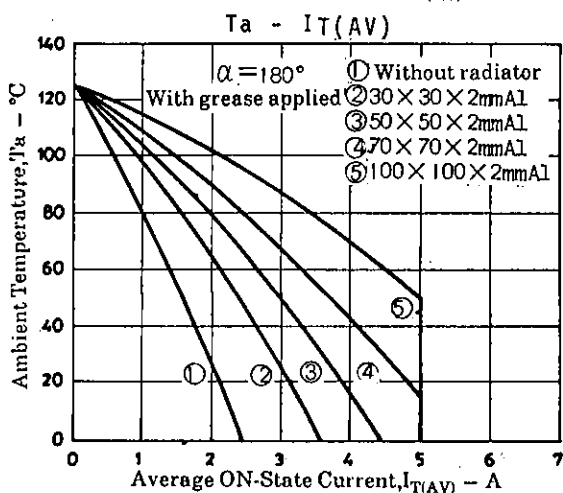
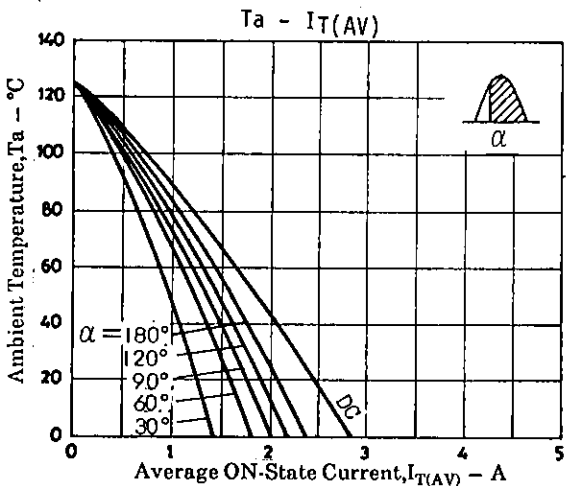
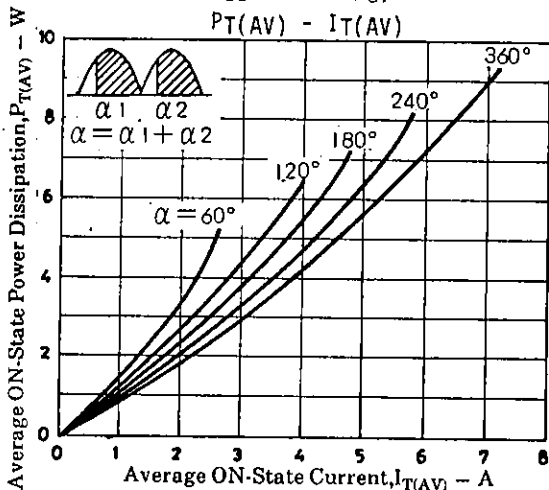
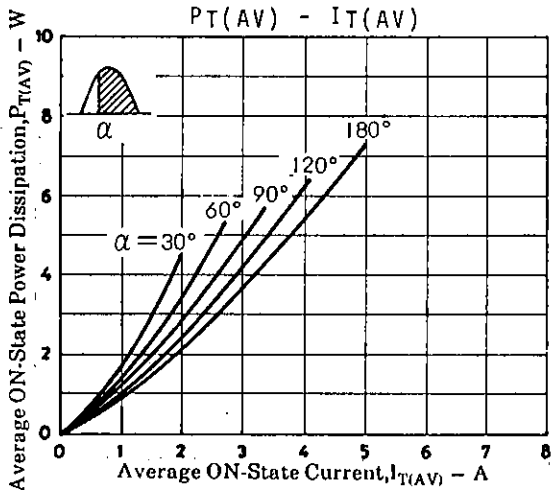
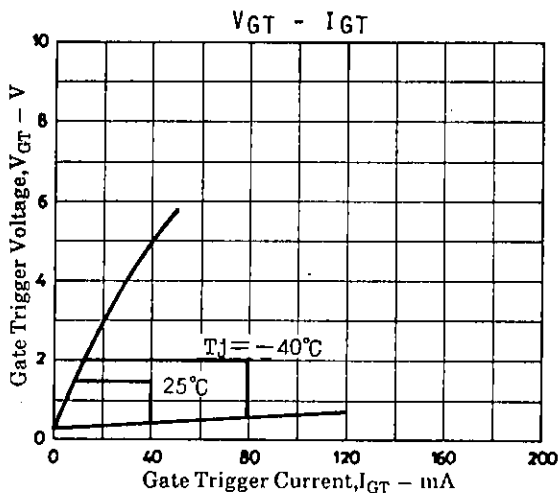
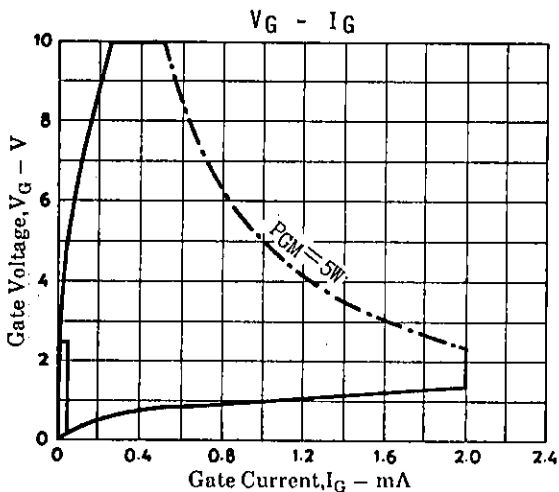
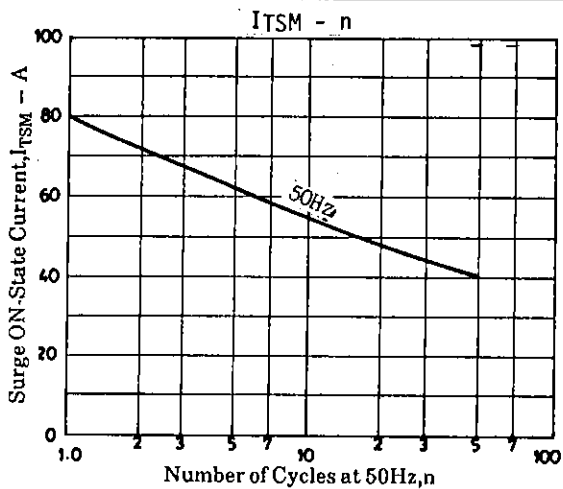
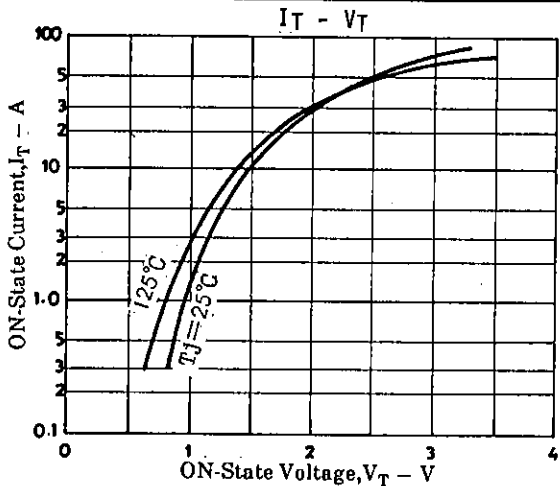
(unit: mm)

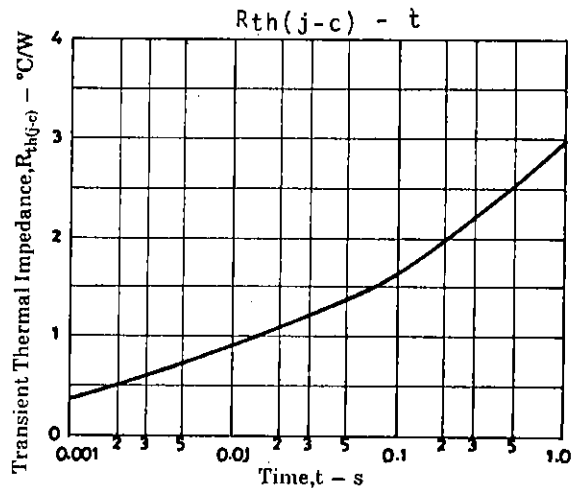
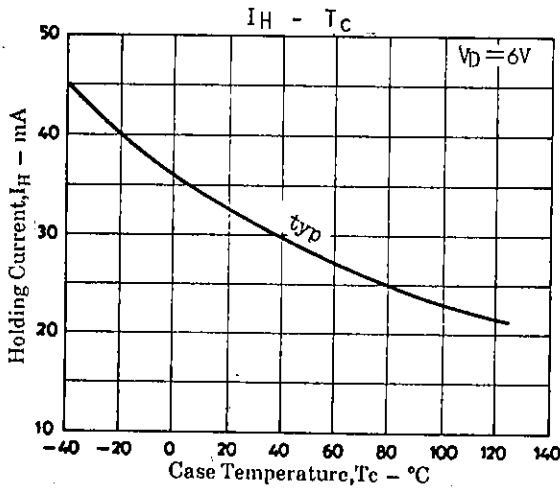
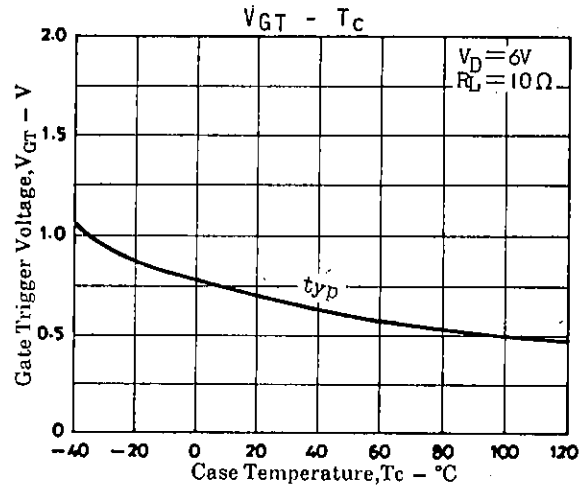
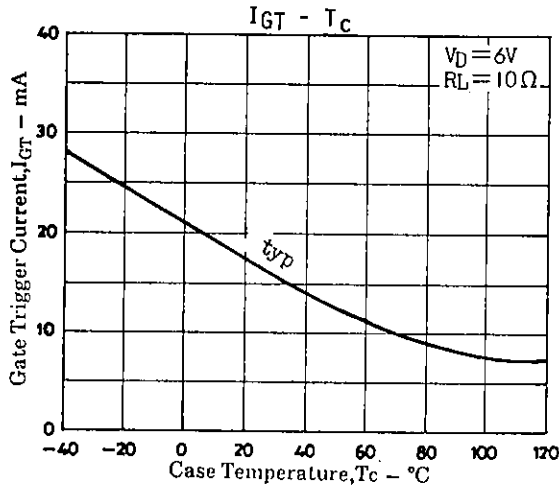
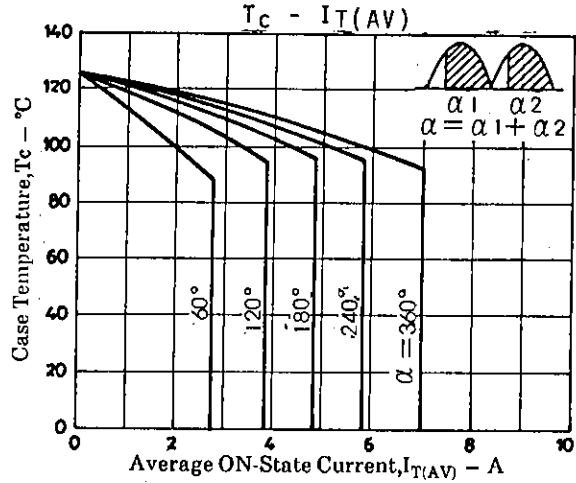
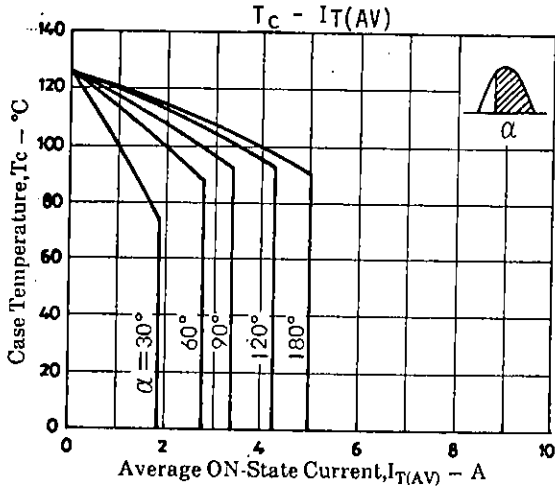


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